

# RF LDMOS Wideband Integrated Power Amplifiers

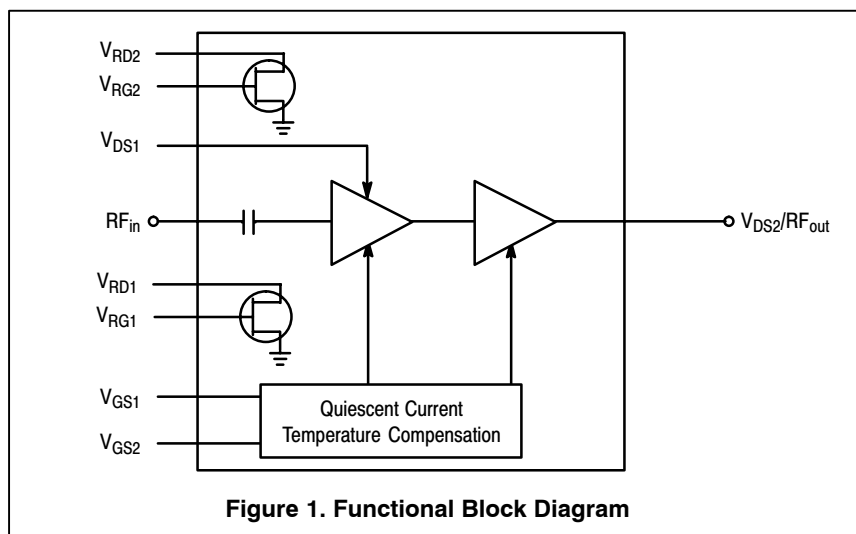
The MWIC930 wideband integrated circuit is designed for CDMA and GSM/GSM EDGE applications. It uses Freescale's newest High Voltage (26 to 28 Volts) LDMOS IC technology and integrates a multi-stage structure. Its wideband On-Chip integral matching circuitry makes it usable from 790 to 1000 MHz. The linearity performances cover all modulations for cellular applications: GSM, GSM EDGE, TDMA, N-CDMA and W-CDMA.

## Final Application

- Typical Performance @ P1dB:  $V_{DD} = 26$  Volts,  $I_{DQ1} = 90$  mA,  $I_{DQ2} = 240$  mA,  $P_{out} = 30$  Watts P1dB, Full Frequency Band (921-960 MHz)  
 Power Gain — 30 dB  
 Power Added Efficiency — 45%

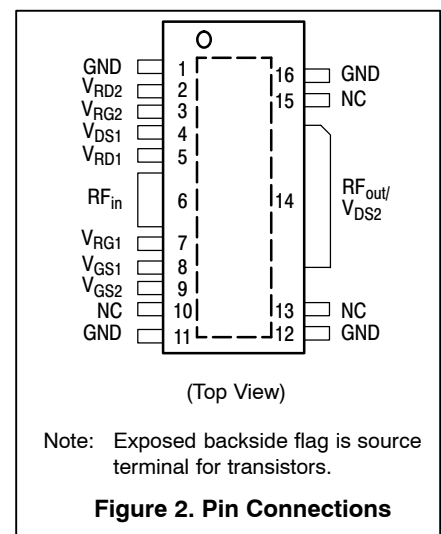
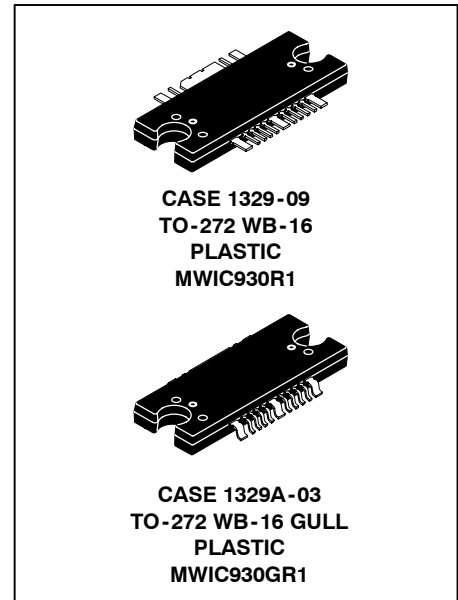
## Driver Application

- Typical Single-Carrier N-CDMA Performance:  $V_{DD} = 27$  Volts,  $I_{DQ1} = 90$  mA,  $I_{DQ2} = 240$  mA,  $P_{out} = 5$  Watts Avg., Full Frequency Band (865-894 MHz), IS -95 (Pilot, Sync, Paging, Traffic Codes 8 Through 13), Channel Bandwidth = 1.2288 MHz. Peak/Avg. = 9.8 dB @ 0.01% Probability on CCDF.  
 Power Gain — 31 dB  
 Power Added Efficiency — 21%  
 ACPR @ 750 kHz Offset — -52 dBc @ 30 kHz Bandwidth
- Capable of Handling 5:1 VSWR, @ 26 Vdc, 921 MHz, 30 Watts CW Output Power
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- On-Chip Matching (50 Ohm Input, DC Blocked, >4 Ohm Output)
- Integrated Quiescent Current Temperature Compensation with Enable/Disable Function
- On-Chip Current Mirror  $g_m$  Reference FET for Self Biasing Application (1)
- Integrated ESD Protection
- Also Available in Gull Wing for Surface Mount
- In Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.



**MWIC930R1**  
**MWIC930GR1**

**746-960 MHz, 30 W, 26-28 V**  
**SINGLE N-CDMA, GSM/GSM EDGE**  
**RF LDMOS WIDEBAND INTEGRATED**  
**POWER AMPLIFIERS**



1. Refer to AN1987/D, *Quiescent Current Control for the RF Integrated Circuit Device Family*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1987.

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +65	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +15	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +175	°C
Operating Junction Temperature	$T_J$	175	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value <sup>(1)</sup>	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
GSM Application ( $P_{out} = 30$ W CW)	Stage 1, 26 Vdc, $I_{DQ} = 90$ mA Stage 2, 26 Vdc, $I_{DQ} = 240$ mA	5.9 1.4	
GSM EDGE Application ( $P_{out} = 15$ W CW)	Stage 1, 27 Vdc, $I_{DQ} = 90$ mA Stage 2, 27 Vdc, $I_{DQ} = 240$ mA	6.5 1.7	
CDMA Application ( $P_{out} = 5$ W CW)	Stage 1, 27 Vdc, $I_{DQ} = 90$ mA Stage 2, 27 Vdc, $I_{DQ} = 240$ mA	6.5 1.8	

**Table 3. ESD Protection Characteristics**

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)
Charge Device Model	C2 (Minimum)

**Table 4. Moisture Sensitivity Level**

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113D, IPC/JEDEC J-STD-020C	3	260	°C

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 27$  Vdc,  $I_{DQ1} = 90$  mA,  $I_{DQ2} = 240$  mA,  $P_{out} = 5$  W Avg. N-CDMA,  $f = 880$  MHz, Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Bandwidth @  $\pm 750$  MHz Offset. Peak/Avg. = 9.8 dB @ 0.01% Probability on CCDF

Power Gain	$G_{ps}$	28	31	—	dB
Power Added Efficiency	PAE	18	21	—	%
Input Return Loss ( $f = 880$ MHz)	IRL	—	-12	-9	dB
Adjacent Channel Power Ratio	ACPR	—	-52	-48	dBc

**Typical Performances** (In Freescale Test Fixture)  $V_{DD} = 26$  Vdc,  $I_{DQ1} = 90$  mA,  $I_{DQ2} = 240$  mA, 840 MHz < Frequency < 920 MHz

Quiescent Current Accuracy over Temperature <sup>(2)</sup> Stage 1 with 33.2 k $\Omega$ Gate Feed Resistors (-30 to 115°C) Stage 2 with 47.5 k $\Omega$ Gate Feed Resistors (-30 to 115°C)	$\Delta I_{1QT}$ $\Delta I_{2QT}$	—	$\pm 2.5$ $\pm 2.5$	—	%
Gain Flatness in 80 MHz Bandwidth @ $P_{out} = 5$ W CW	$G_F$	—	0.3	—	dB
Deviation from Linear Phase in 80 MHz Bandwidth @ $P_{out} = 5$ W CW	$\Phi$	—	0.6	—	°
Delay @ $P_{out} = 5$ W CW Including Output Matching	Delay	—	3	—	ns
Part-to-Part Phase Variation @ $P_{out} = 5$ W CW	$\Delta\Phi$	—	$\pm 15$	—	°

1. Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>.

Select Documentation/Application Notes - AN1955.

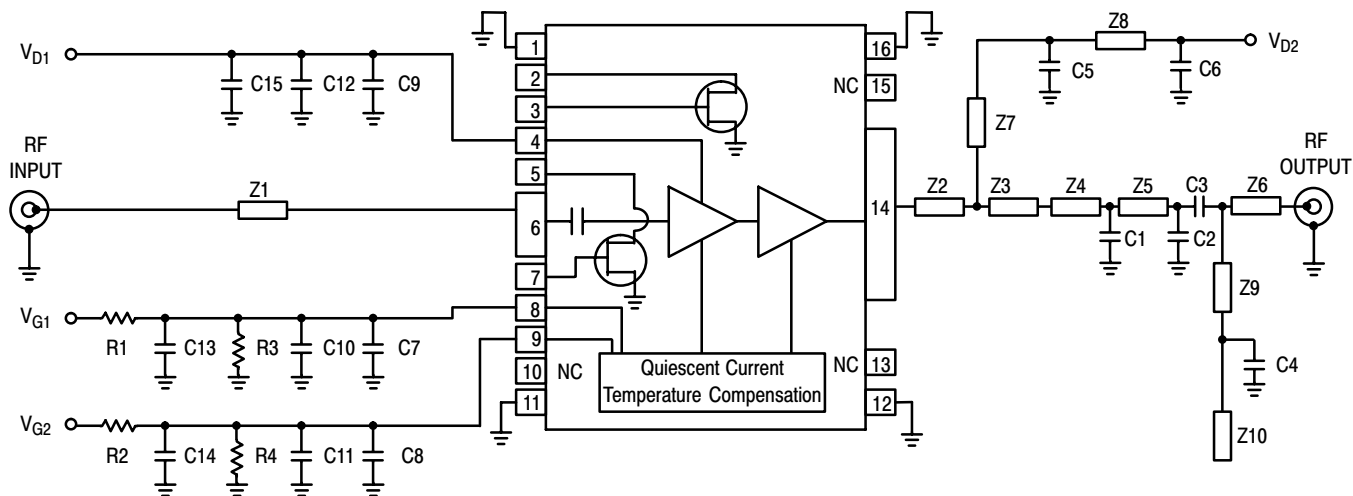
2. Refer to AN1977/D, *Quiescent Current Thermal Tracking Circuit in the RF Integrated Circuit Family*. Go to <http://www.freescale.com/rf>.

Select Documentation/Application Notes - AN1977.

(continued)

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$ , unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Typical GSM/GSM EDGE Performances</b> (In Freescale GSM/GSM EDGE Test Fixture, 50 ohm system) $V_{DD} = 27\text{ Vdc}$ , $I_{DQ1} = 90\text{ mA}$ , $I_{DQ2} = 240\text{ mA}$ , 921 MHz < Frequency < 960 MHz					
Output Power, 1dB Compression Point	P1dB	—	30	—	W
Power Gain @ $P_{out} = 30\text{ W CW}$	$G_{ps}$	—	30	—	dB
Power Added Efficiency @ $P_{out} = 30\text{ W CW}$	PAE	—	45	—	%
Input Return Loss @ $P_{out} = 30\text{ W CW}$	IRL	—	-12	—	dB
Intermodulation Distortion (15 W, 2-Tone, 100 kHz Tone Spacing)	IMD	—	-30	—	dBc
Intermodulation Distortion (1 W, 2-Tone, 100 kHz Tone Spacing)	IMD backoff	—	-45	—	dBc
Gain Flatness in a 40 MHz Bandwidth @ $P_{out} = 30\text{ W CW}$	$G_F$	—	0.3	—	dB
Deviation from Linear Phase in a 40 MHz Bandwidth @ $P_{out} = 30\text{ W CW}$	$\Phi$	—	0.6	—	°



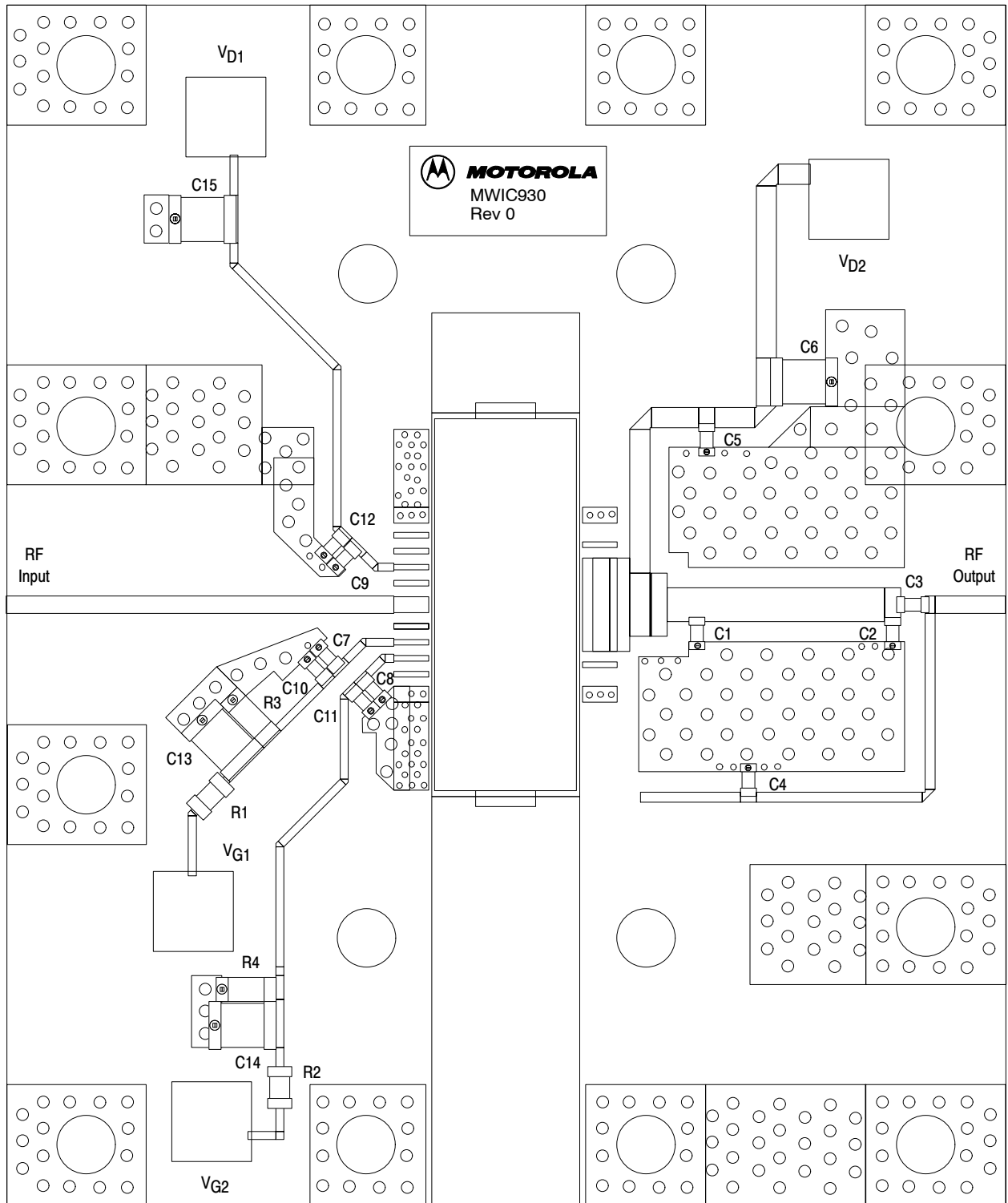
Z1	0.0438" x 0.970" 50 Ω Microstrip (not including lead pad)	Z6	0.0438" x 0.2009" Microstrip
Z2	0.234" x 0.1183" Microstrip (including lead pad)	Z7	0.5274" x 0.0504" Microstrip
Z3	0.1575" x 0.9379" Microstrip	Z8	0.0504" x 0.250" Microstrip
Z4	0.08425" x 0.0729" Microstrip	Z9	0.880" x 0.0254" Microstrip
Z5	0.08425" x 0.5111" Microstrip	Z10	0.0254" x 0.250" Microstrip
		PCB	Rogers 4350, 0.020", $\epsilon_r = 3.50$

**Figure 3. MWIC930R1(GR1) Test Fixture Schematic**

**Table 6. MWIC930R1(GR1) Test Fixture Component Designations and Values**

Part	Description	Part Number	Manufacturer
*C1	15 pF High Q Capacitor	ATC600S150JW	ATC
*C2	6.8 pF High Q Capacitor - GSM Fixture 8.2 pF High Q Capacitor - CDMA Fixture	ATC600S6R8CW ATC600S8R2CW	ATC
*C3	5.6 pF High Q Capacitor	ATC600S5R6CW	ATC
*C4, C5, C7, C8, C9	47 pF High Q Capacitors	ATC600S470JW	ATC
C6, C13, C14, C15	1 μF Chip Capacitors	GRM42-2X7R105K050AL	Murata
C10, C11, C12	10 nF Chip Capacitors	C0603C103J5R	Kemet
R1, R2	1 kΩ, 1/8 W Chip Resistors	RM73B2AT102J	KOA Speer
R3, R4	1 MΩ, 1/4 W Chip Resistors	RM73B2BT105J	KOA Speer

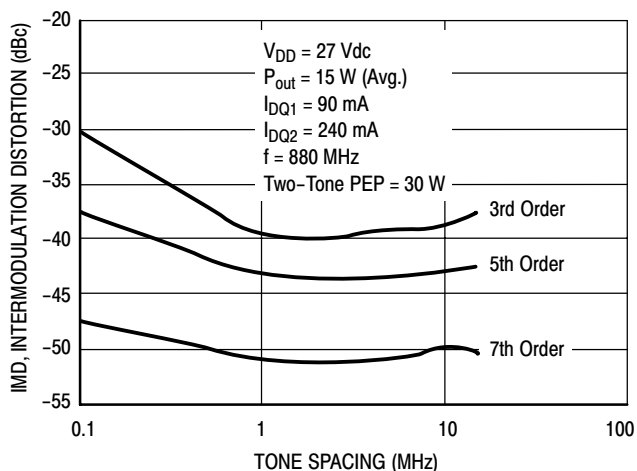
\* For output matching and bypass purposes, it is strongly recommended to use these exact capacitors.



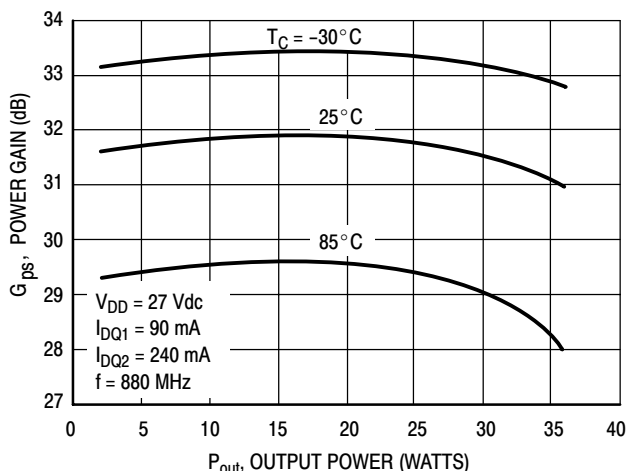
Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

**Figure 4. MWIC930R1(GR1) Test Circuit Component Layout**

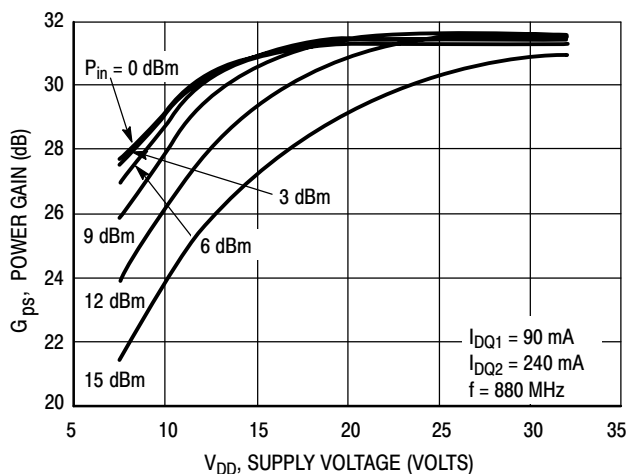
## TYPICAL CHARACTERISTICS



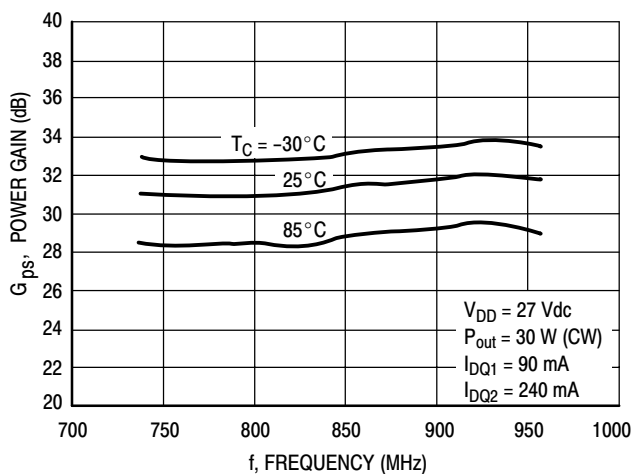
**Figure 5. Intermodulation Distortion Products versus Output Power**



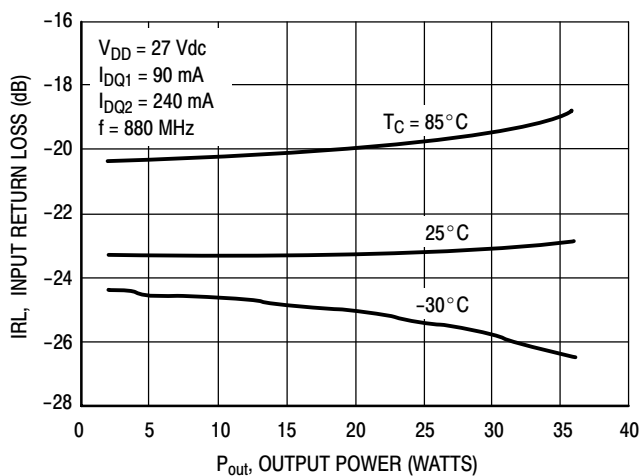
**Figure 6. Power Gain versus Output Power**



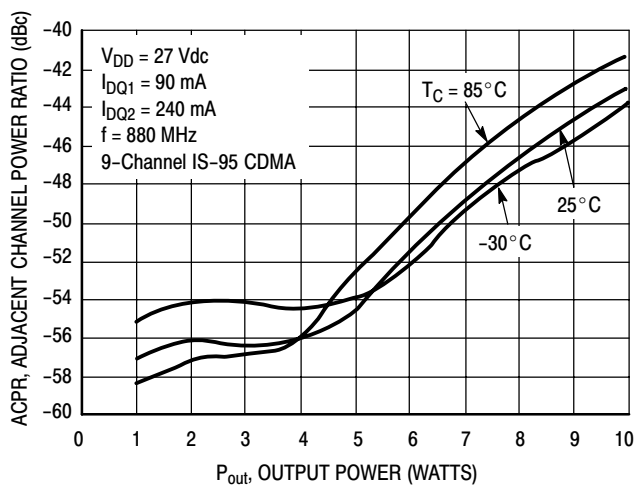
**Figure 7. Power Gain versus Supply Voltage**



**Figure 8. Power Gain versus Frequency**

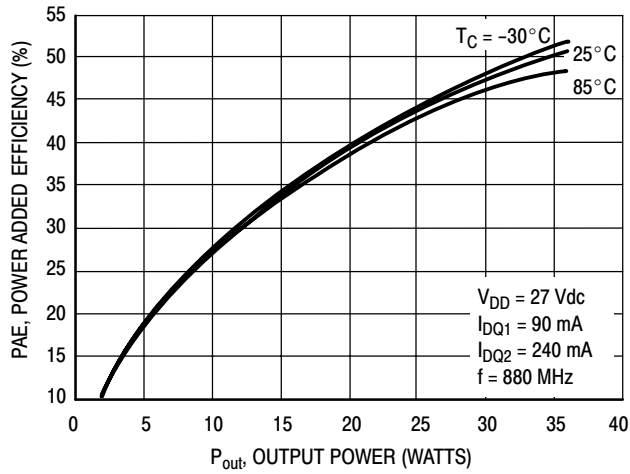


**Figure 9. Input Return Loss versus Output Power**

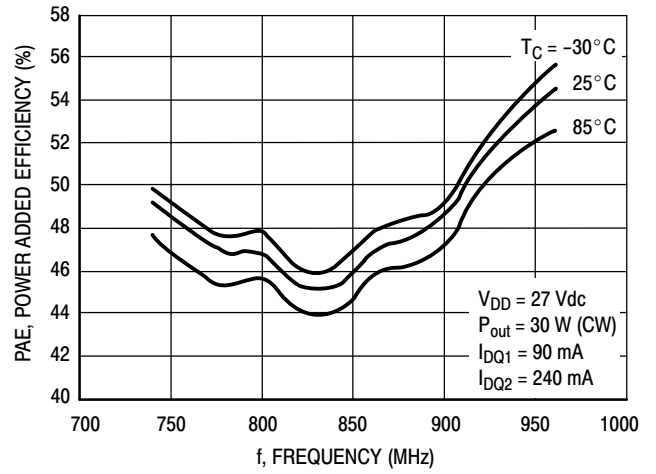


**Figure 10. Adjacent Channel Power Ratio versus Output Power**

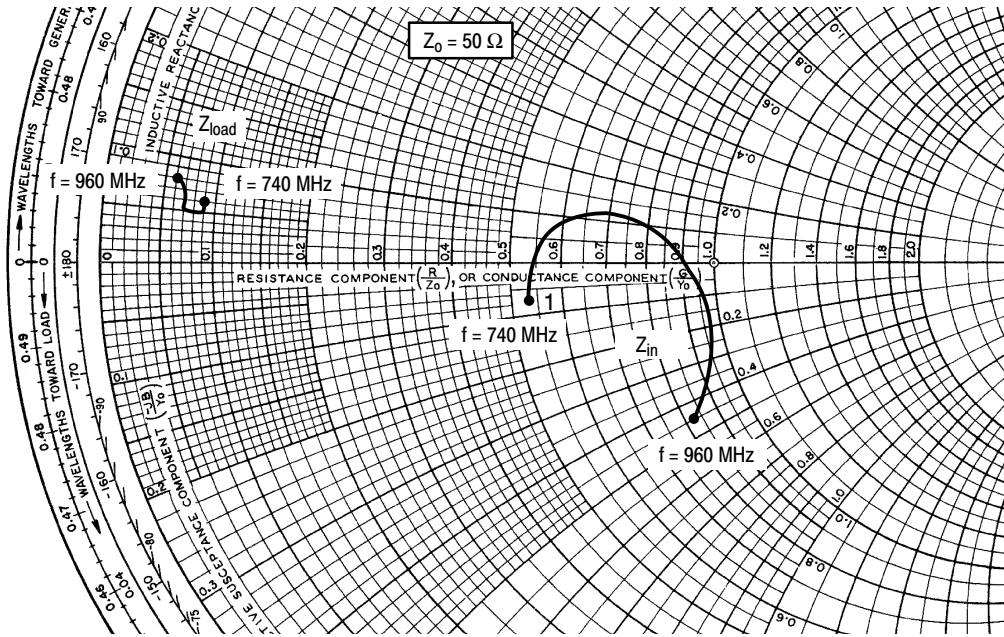
## TYPICAL CHARACTERISTICS



**Figure 11. Power Added Efficiency versus Output Power**



**Figure 12. Power Added Efficiency versus Frequency**



$V_{DD} = 27 \text{ Vdc}$ ,  $I_{DQ1} = 90 \text{ mA}$ ,  $I_{DQ2} = 240 \text{ mA}$ ,  $P_{out} = 5 \text{ W Avg.}$

f MHz	$Z_{in}$ $\Omega$	$Z_{load}$ $\Omega$
740	$26.61 - j3.68$	$4.28 + j2.99$
760	$26.88 - j0.53$	$4.37 + j2.91$
780	$28.22 + j2.21$	$4.39 + j2.79$
800	$30.57 + j4.31$	$4.34 + j2.64$
820	$33.79 + j5.53$	$4.21 + j2.54$
840	$37.83 + j5.30$	$4.06 + j2.52$
860	$41.92 + j3.42$	$3.90 + j2.58$
880	$45.58 - j0.40$	$3.73 + j2.70$
900	$47.77 - j5.84$	$3.59 + j2.93$
920	$47.83 - j12.15$	$3.43 + j3.17$
940	$45.55 - j18.05$	$3.28 + j3.44$
960	$41.58 - j22.64$	$3.13 + j3.75$

$Z_{in}$  = Device input impedance as measured from RF input to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

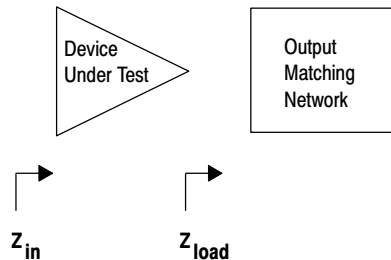
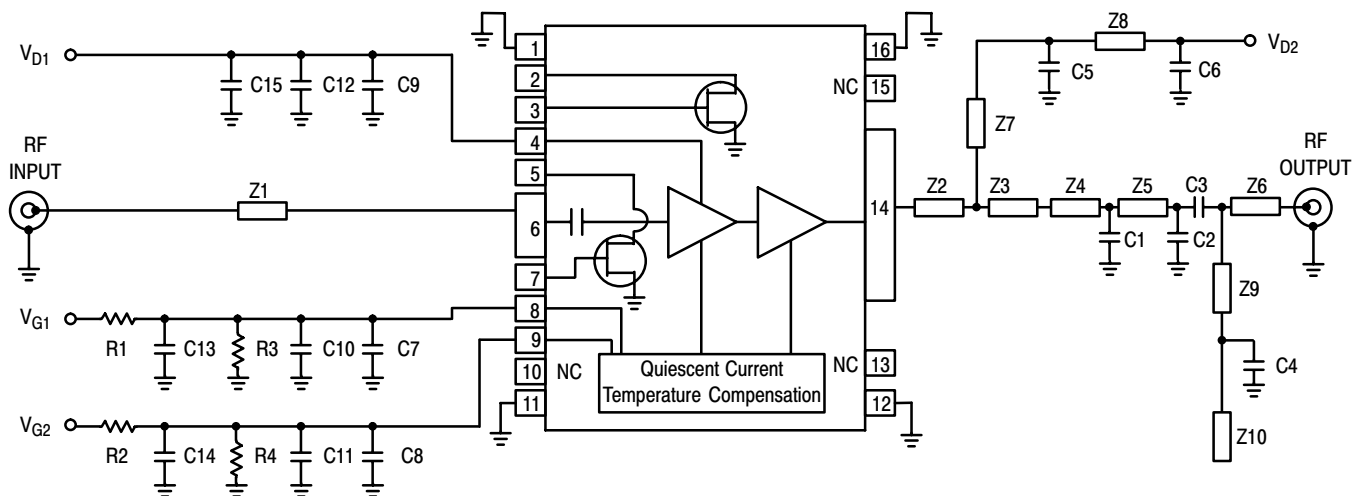


Figure 13. Series Equivalent Input and Load Impedance

## DRIVER/PRE-DRIVER PERFORMANCE



Z1	0.0438" x 0.970" 50 Ω Microstrip (not including lead pad)	Z6	0.0438" x 0.2009" Microstrip
Z2	0.234" x 0.1183" Microstrip (including lead pad)	Z7	0.5274" x 0.0504" Microstrip
Z3	0.1575" x 0.9379" Microstrip	Z8	0.0504" x 0.250" Microstrip
Z4	0.08425" x 0.0729" Microstrip	Z9	0.880" x 0.0254" Microstrip
Z5	0.08425" x 0.5111" Microstrip	Z10	0.0254" x 0.250" Microstrip
		PCB	Rogers 4350, 0.020", $\epsilon_r = 3.50$

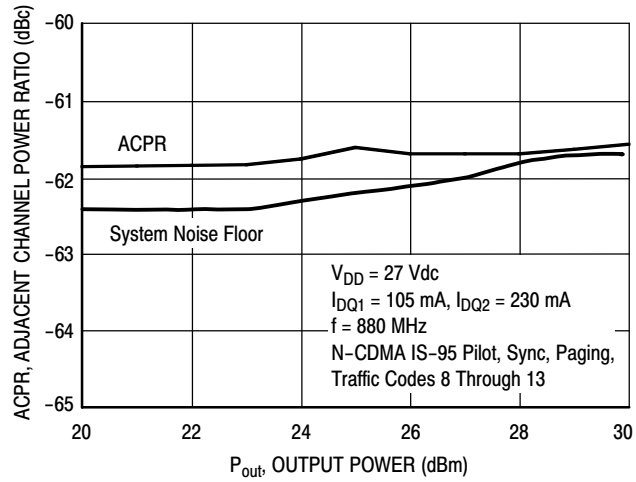
**Figure 14. MWIC930R1 (GR1) Test Fixture Schematic —  
Alternate Characterization for Driver/Pre-Driver Performance**

**Table 7. MWIC930R1 (GR1) Test Fixture Component Designations and Values —  
Alternate Characterization for Driver/Pre-Driver Performance**

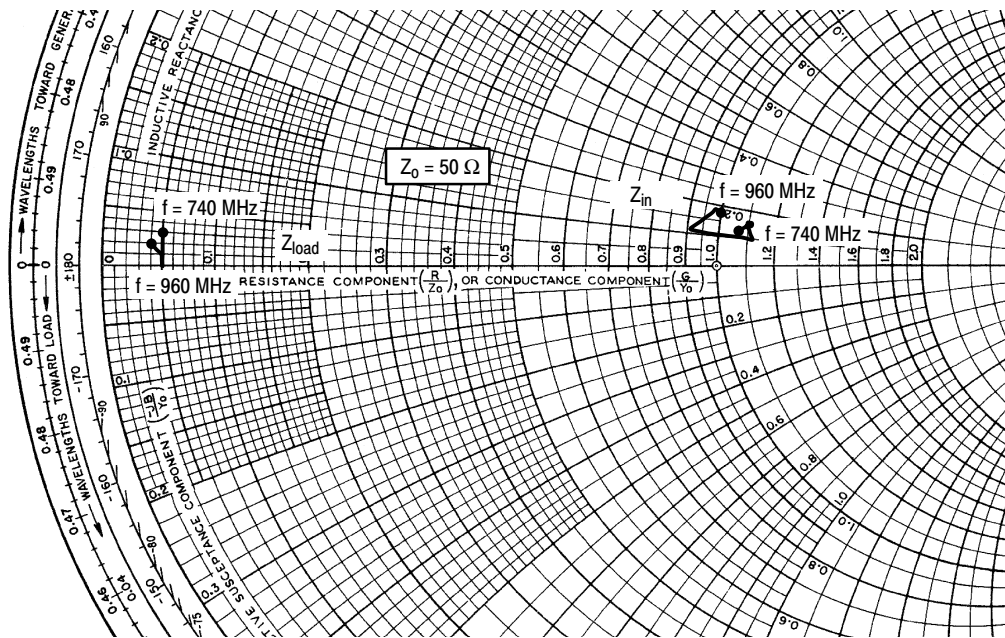
Part	Description	Part Number	Manufacturer
*C1	12 pF High Q Capacitor	ATC600S120JW	ATC
*C2	8.2 pF High Q Capacitor - CDMA Fixture	ATC600S8R2CW	ATC
*C3	5.6 pF High Q Capacitor	ATC600S5R6CW	ATC
*C4, C5, C7, C8, C9	47 pF High Q Capacitors	ATC600S470JW	ATC
C6, C13, C14, C15	1 μF Chip Capacitors	GRM42-2X7R105K050AL	Murata
C10, C11, C12	10 nF Chip Capacitors	C0603C103J5R	Kemet
R1, R2	1 kΩ, 1/8 W Chip Resistors	RM73B2AT102J	KOA Speer
R3, R4	1 MΩ, 1/4 W Chip Resistors	RM73B2BT105J	KOA Speer

\*For output matching and bypass purposes, it is strongly recommended to use these exact capacitors.

**TYPICAL CHARACTERISTICS  
DRIVER/PRE-DRIVER PERFORMANCE**



**Figure 15. Single-Carrier N-CDMA ACPR versus Output Power**

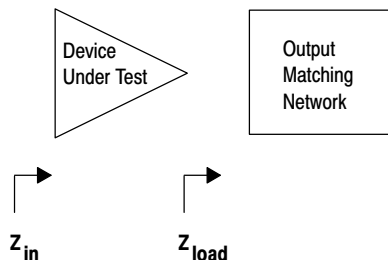


$V_{DD} = 27 \text{ Vdc}$ ,  $I_{DQ1} = 105 \text{ mA}$ ,  $I_{DQ2} = 230 \text{ mA}$ ,  $P_{out} = 5 \text{ W Avg.}$

f MHz	$Z_{in}$ $\Omega$	$Z_{load}$ $\Omega$
740	$53.944 + j6.745$	$2.535 + j1.662$
760	$54.452 + j7.112$	$2.602 + j1.080$
780	$55.006 + j7.440$	$2.688 + j0.548$
800	$55.549 + j7.656$	$2.659 + j0.064$
820	$55.604 + j7.855$	$2.615 + j0.329$
840	$55.190 + j7.835$	$2.568 + j0.450$
860	$55.110 + j7.410$	$2.494 + j0.620$
880	$55.752 + j4.763$	$2.444 + j0.650$
900	$45.606 + j5.832$	$2.440 + j0.689$
920	$49.206 + j9.284$	$2.134 + j0.930$
940	$49.939 + j9.030$	$2.155 + j0.835$
960	$50.088 + j8.752$	$2.095 + j1.235$

$Z_{in}$  = Device input impedance as measured from RF input to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.



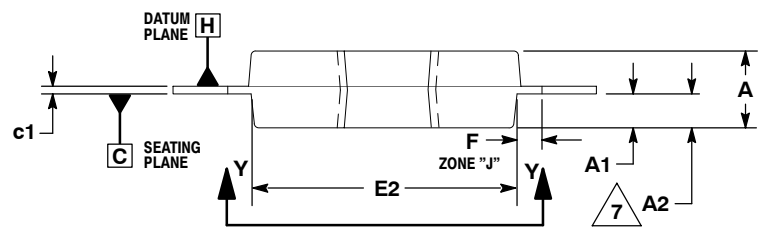
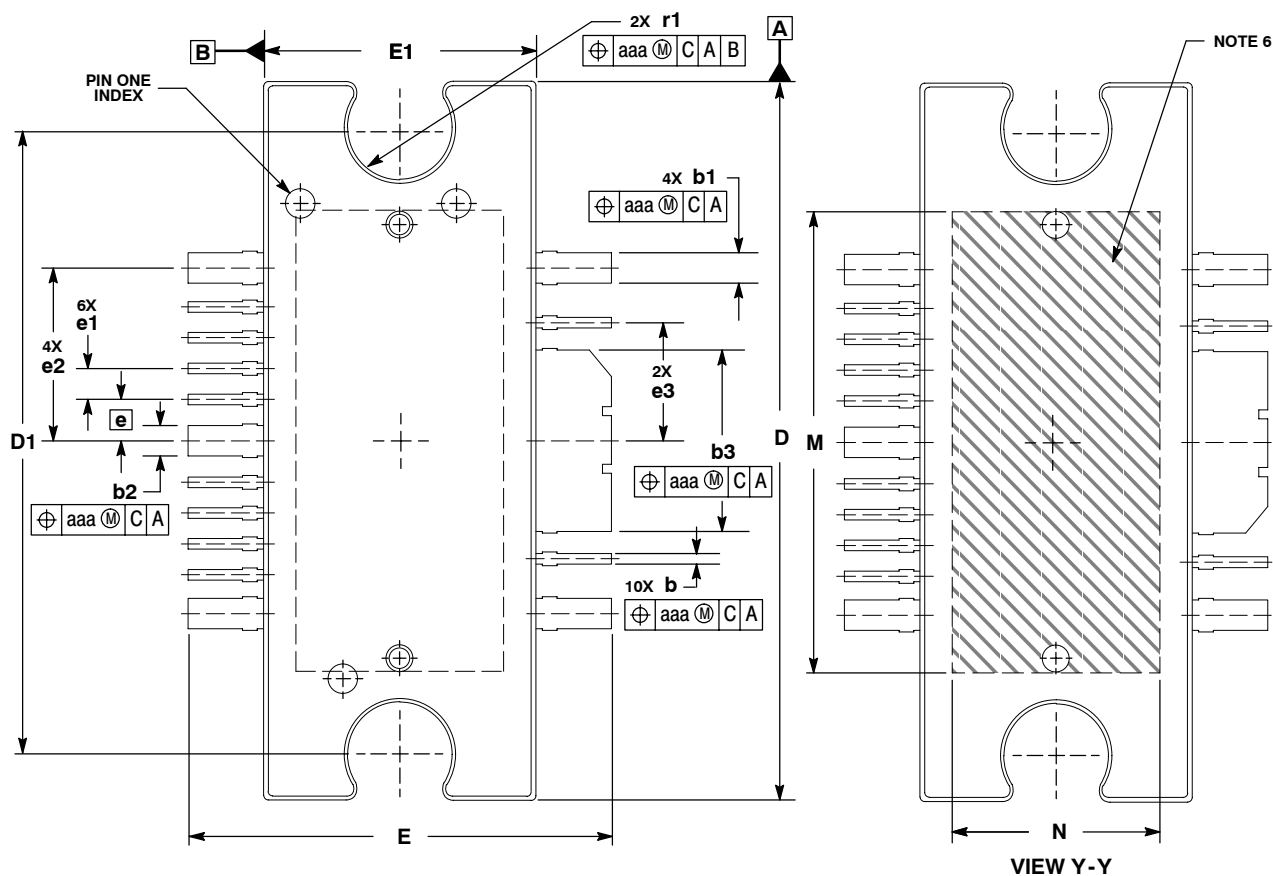
**Figure 16. Series Equivalent Input and Load Impedance — Alternate Characterization for Driver/Pre-Driver Performance**

# NOTES



# NOTES

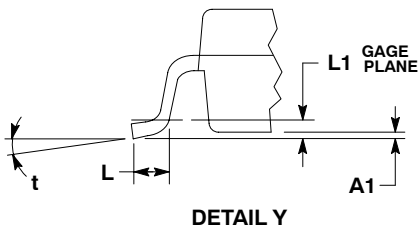
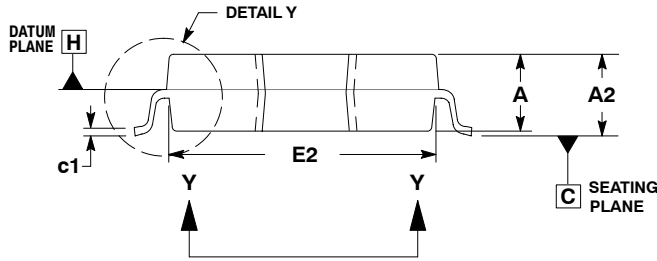
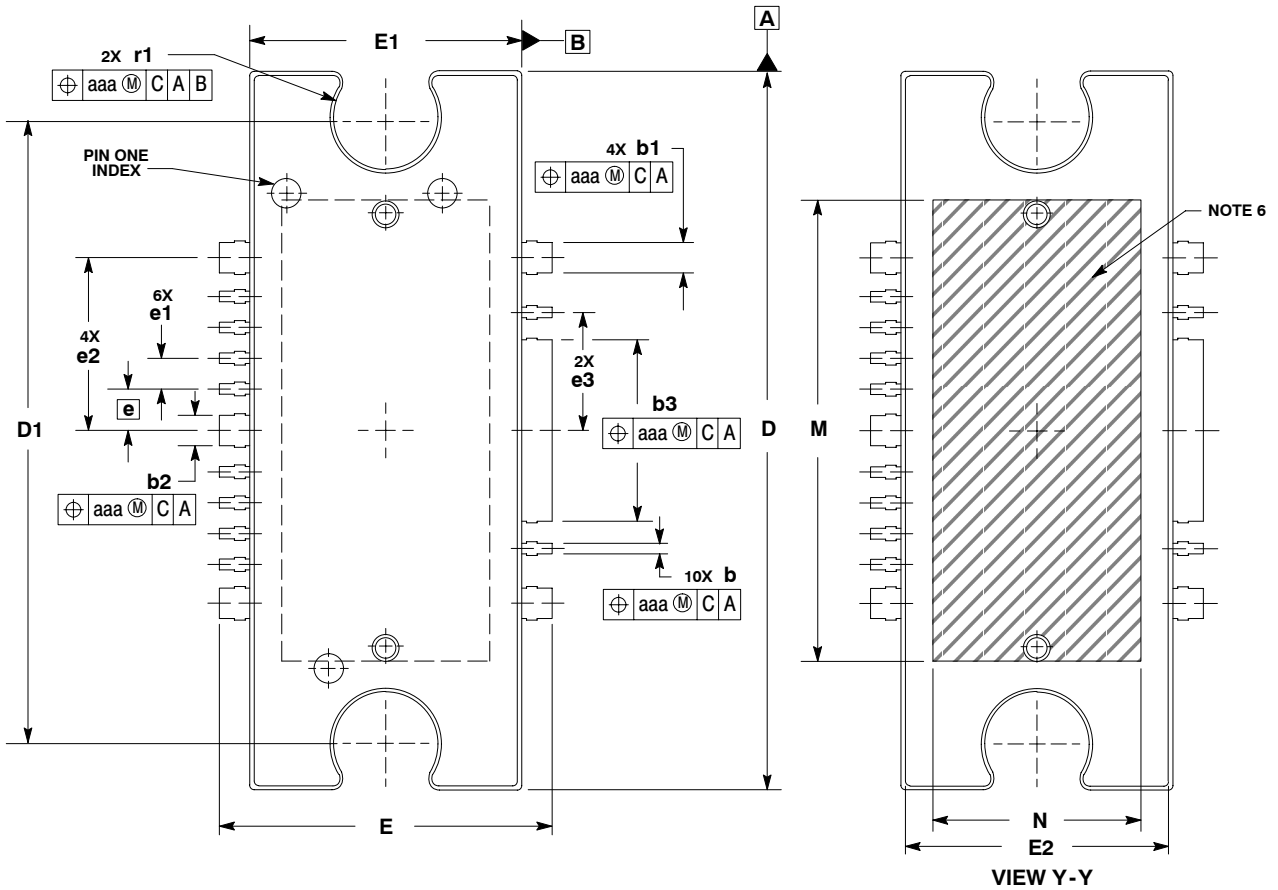
# PACKAGE DIMENSIONS



- NOTES:
1. CONTROLLING DIMENSION: INCH.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
  3. DATUM PLANE -H- IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
  4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 (0.15) PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
  5. DIMENSIONS "b", "b1", "b2" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 (0.13) TOTAL IN EXCESS OF THE "b", "b1", "b2" AND "b3" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
  6. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.
  7. DIM A2 APPLIES WITHIN ZONE "J" ONLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.038	.044	0.96	1.12
A2	.040	.042	1.02	1.07
D	.928	.932	23.57	23.67
D1	.810 BSC		20.57 BSC	
E	.551	.559	14.00	14.20
E1	.353	.357	8.97	9.07
E2	.346	.350	8.79	8.89
F	.025 BSC		0.64 BSC	
M	.600	---	15.24	---
N	.270	---	6.86	---
b	.011	.017	0.28	0.43
b1	.037	.043	0.94	1.09
b2	.037	.043	0.94	1.09
b3	.225	.231	5.72	5.87
c1	.007	.011	.18	.28
e	.054 BSC		1.37 BSC	
e1	.040 BSC		1.02 BSC	
e2	.224 BSC		5.69 BSC	
e3	.150 BSC		3.81 BSC	
r1	.063	.068	1.6	1.73
aaa	.004		.10	

**CASE 1329-09  
ISSUE J  
TO-272 WB-16  
PLASTIC  
MWIC930R1**



- NOTES:
1. CONTROLLING DIMENSION: INCH.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
  3. DATUM PLANE -H- IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
  4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 (0.15) PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
  5. DIMENSIONS "b", "b1", "b2" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 (0.13) TOTAL IN EXCESS OF THE "b", "b1", "b2" AND "b3" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
  6. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SINK.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.001	.004	0.02	0.10
A2	.099	.110	2.51	2.79
D	.928	.932	23.57	23.67
D1	.810 BSC		20.57 BSC	
E	.429	.437	10.90	11.10
E1	.353	.357	8.97	9.07
E2	.346	.350	8.79	8.89
L	.018	.024	4.90	5.06
L1	.01 BSC		0.25 BSC	
M	.600	---	15.24	---
N	.270	---	6.86	---
b	.011	.017	0.28	0.43
b1	.037	.043	0.94	1.09
b2	.037	.043	0.94	1.09
b3	.225	.231	5.72	5.87
c1	.007	.011	.18	.28
e	.054 BSC		1.37 BSC	
e1	.040 BSC		1.02 BSC	
e2	.224 BSC		5.69 BSC	
e3	.150 BSC		3.81 BSC	
r1	.063	.068	1.6	1.73
t	2°	8°	2°	8°
aaa	.004		.10	

**CASE 1329A-03  
ISSUE B  
TO-272 WB-16 GULL  
PLASTIC  
MWIC930GR1**

MWIC930R1 MWIC930GR1

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